# PATENT COOPERATION TREAT



## **PCT**

### INTERNATIONAL PRELIMINARY EXAMINATION REPORT

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INTERNATIO	ONAL PRELIMINARY EX	AMINATION REPORT	
	(PCT Article 36 and Ru	ıle 70)	
Applicant's or agent's file reference PHCF-03037	I DOD ETIDTITED ACTION	e Notification of Transmittal eliminary Examination Report (For	
International application No. PCT/JP2003/008173	International filing date (day/mont. 26 June 2003 (26.06.200		-
International Patent Classification (IPC) or no C30B 29/38, H01L 21/205	<u> </u>	20 0 0 0 0 0	
Applicant	HITACHI CABLE, LT	D.	
This international preliminary examinary examinary.		this International Preliminary Exan	nining Authorit
and is transmitted to the applicant ac			
2. This REPORT consists of a total of	_		
amended and are the basis for	ied by ANNEXES, i.e., sheets of the r this report and/or sheets containing Administrative Instructions under the	g rectifications made before this A	
	tal of1 sheets.		
This report contains indications relat	ting to the following items:		
I Basis of the report			
II Priority			
III Non-establishment of	of opinion with regard to novelty, in	ventive step and industrial applicab	ility
IV Lack of unity of inve	ention		
V Reasoned statement citations and explana	under Article 35(2) with regard to nations supporting such statement	lovelty, inventive step or industrial	applicability;
VI Certain documents of	rited	,	
VII Certain defects in th	e international application		
VIII Certain observations	s on the international application		
Date of submission of the demand	Date of cor	mpletion of this report	
15 December 2003 (15.1)	2.2003)	13 April 2004 (13.04.20	)04)
Name and mailing address of the IPEA/JP	Authorized	l officer	
Facsimile No.	Telephone	No.	

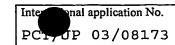
Form PCT/IPEA/409 (cover sheet) (July 1998)

## INTERNATIONAL PRELIMINARY EXAMINATION REPORT

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Int	onal application No.
	PCT/JP2003/008173

I.	Basis	of the re	eport		
1.	With	regard to	to the elements of the international application:*		<del></del>
		the inte	ernational application as originally filed		
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		pages	1-12	, as	s originally filed
		pages			
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		pages	1-9, 11-14		
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<b>2.</b>	the ir	nternation e element the lang the lang	to the language, all the elements marked above were ava- onal application was filed, unless otherwise indicated unde- nts were available or furnished to this Authority in the foll- nguage of a translation furnished for the purposes of interranguage of publication of the international application (und- nguage of the translation furnished for the purposes of in- 3).	er this item. owing language national search (under Rule 23.1(b)). er Rule 48.3(b)).	which is:
3.	With prelin	minary ex	I to any nucleotide and/or amino acid sequence di examination was carried out on the basis of the sequence I med in the international application in written form.	isclosed in the international application, tisting:	he international
	Ш		ogether with the international application in computer read	dable form.	
furnished subsequently to this Authority in written form.					
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			statement that the subsequently furnished written sequational application as filed has been furnished.	uence listing does not go beyond the di	sclosure in the
	Ш		tatement that the information recorded in computer rea furnished.	dable form is identical to the written sequ	ence listing has
4.		The am	mendments have resulted in the cancellation of:		
			the description, pages		
			the claims, Nos.		
			the drawings, sheets/fig		
5.			eport has been established as if (some of) the amendment of the disclosure as filed, as indicated in the Supplemental I		considered to go
*	in th	ncement s is report 10.17).	sheets which have been furnished to the receiving Office rt as "originally filed" and are not annexed to this r	in response to an invitation under Article I- eport since they do not contain amendme	4 are referred to nts (Rule 70.16
**		•	nent sheet containing such amendments must be referred to	o under item 1 and annexed to this report.	
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#### INTERNATIONAL PREI



l	v.	Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability;
ı		citations and explanations supporting such statement

. Statement			
Novelty (N)	Claims	6, 8, 9, 12, 14	YES
	Claims	1-5, 7, 10, 11, 13	NO
Inventive step (IS)	Claims	6, 8, 9, 12, 14	YES
	Claims	1-5, 7, 10, 11, 13	_ NO
Industrial applicability (IA)	Claims	1-14	YES
	Claims		NO

#### 2. Citations and explanations

Document 1: US 5656832 A (Kabushiki Kaisha Toshiba), 12

August 1997

Document 2: JP 4-12092 A (Sumitomo Electric Ind., Ltd.),

16 January 1992

#### Claims 1-4

The invention set forth in claims 1-4 lacks novelty in the light of document 2 cited in the international search report.

Document 2 discloses a porous substrate equipped with a porous layer and a conversion layer, wherein the surface of the conversion layer differs from the porous layer below in that only openings with a diameter of approximately 10Å are formed therein. Therefore, the diameters of the openings in the conversion layer that is disposed upon the outermost surface are smaller than the diameters of the openings in the porous layer.

#### Claim 5

The invention set forth in claim 5 lacks novelty in the light of document 2 cited in the international search report.

Document 2 discloses a feature wherein the porous layer comprises silicon, which is one type of metal.

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#### Claim 6

The invention set forth in claim 6 involves an inventive step in relation to documents 1 and 2 cited in the international search report.

Document 2 does not disclose a feature wherein the porous layer comprises a "metal oxide, a metal nitride or a metal carbide," and even a person skilled in the art could not easily have conceived of this feature in the light of the nitride buffer layer that is disclosed in document 1.

#### Claim 7

The invention set forth in claim 7 lacks novelty in the light of document 2 cited in the international search report.

Document 2 discloses a feature wherein the porous layer comprises silicon, which is a semiconductor material.

#### Claim 8

The invention set forth in claim 8 involves an inventive step in relation to documents 1 and 2 cited in the international search report.

Document 2 does not disclose a feature wherein the porous layer comprises a "semiconductor material configured from a Group III nitride-based compound," and even a person skilled in the art could not easily have conceived of this feature in the light of the nitride buffer layer that is disclosed in document 1.

#### Claim 9

The invention set forth in claim 9 involves an inventive step in relation to documents 1 and 2 cited in the international search report.

Document 2 does not disclose features wherein the conversion layer comprises "TiN or Pt" and the porous layer comprises "GaN," and even a person skilled in the art could not easily have conceived of these features in the light of the nitride buffer layer that is disclosed in document 1.

#### Claim 10

The invention set forth in claim 10 lacks novelty in the light of document 2 cited in the international search report.

Document 2 discloses a feature wherein the openings in the conversion layer have a diameter of approximately 10Å.

#### Claim 11

The invention set forth in claim 11 lacks novelty in the light of document 2 cited in the international search report.

Document 2 discloses a feature wherein the thickness of the conversion layer is approximately  $0.5\mu m$ .

#### Claims 12 and 14

The invention set forth in claims 12 and 14 involves an inventive step in relation to documents 1 and 2 cited in the international search report.

Documents 1 and 2 do not disclose the feature of adding "thermal processing," and even a person skilled in the art could not easily have conceived of this feature in the light of the anodization method that is disclosed in document 2.

#### Claim 13

The invention set forth in claim 13 lacks novelty in the light of document 2 cited in the international search

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report.

The substrate disclosed in document 2 can be used to form compound semiconductor layers, including GaN-based semiconductor layers.